



#### 20V P-Channel Enhancement Mode MOSFET

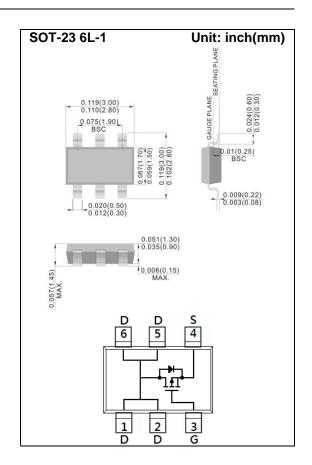
Voltage -20 V Current -6.5A

#### **Features**

- RDS(ON), VGS@-4.5V, ID@-6.5A<35mΩ
- RDS(ON) , VGS@-2.5V, ID@-4.6A<40mΩ</li>
- RDS(ON), VGS@-1.8V, ID@-2.6A<50mΩ
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

#### **Mechanical Data**

- Case: SOT-23 6L-1 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.0141 grams
- Marking: S17



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	-20	V
Gate-Source Voltage		V <sub>G</sub> s	<u>+</u> 8	V
Continuous Drain Current		I <sub>D</sub>	-6.5	Α
Pulsed Drain Current		I <sub>DM</sub>	-26	А
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	2	W
	Derate above 25°C		16	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance				
- Junction to Ambient (Note 3)		R <sub>θJA</sub>	62.5	°C/W





### **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	-	ı	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-0.35	-0.59	-0.9	<b>V</b>
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6.5A	-	29	35	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-4.6A	-	33	40	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-2.6A	-	40	50	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-0.01	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	<u>+</u> 10	<u>+</u> 100	nA
Dynamic						
Total Gate Charge	$Q_g$	V <sub>DS</sub> =-10V, I <sub>D</sub> =-6.5A, V <sub>GS</sub> =-4.5V (Note 1,2)	-	18.9	ı	nC
Gate-Source Charge	$Q_gs$		-	2.8	-	
Gate-Drain Charge	$Q_{gd}$		-	4.2	ı	
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	1760	-	pF
Output Capacitance	Coss		-	148	ı	
Reverse Transfer Capacitance	Crss		-	120	-	
Switching						
Turn-On Delay Time	td <sub>(on)</sub>	$\begin{array}{c} V_{DS}\text{=-}10V,\ I_{D}\text{=-}6.5A, \\ V_{GS}\text{=-}4.5V, \\ R_{G}\text{=-}6\Omega \ ^{\text{(Note 1.2)}} \end{array}$	-	12	-	ns
Turn-On Rise Time	tr			68		
Turn-Off Delay Time	td <sub>(off)</sub>		-	82	-	
Turn-Off Fall Time	tf		-	35	ı	
Drain-Source Diode						
Maximum Continuous Drain-Source	la				-2.0	Α
Diode Forward Current	Is		_	-	-∠.∪	А
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	-0.69	-1.2	V

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
- 4. The maximum current rating is package limited





#### **TYPICAL CHARACTERISTIC CURVES**

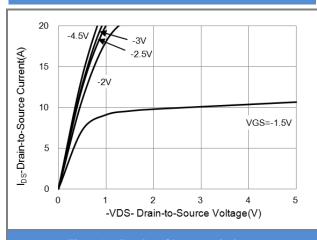
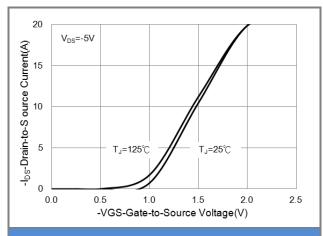


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

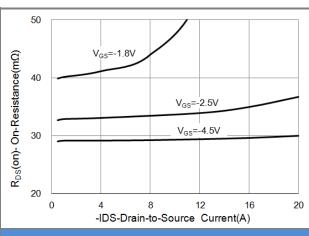


Fig.3 On-Resistance vs. Drain Current

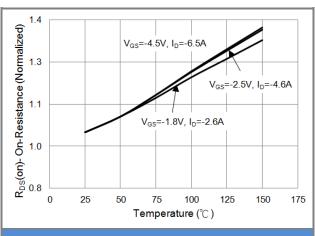


Fig.4 On-Resistance vs. Junction temperature

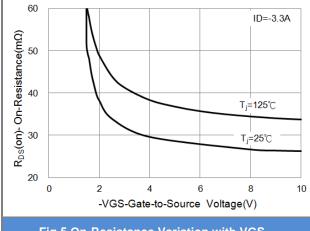
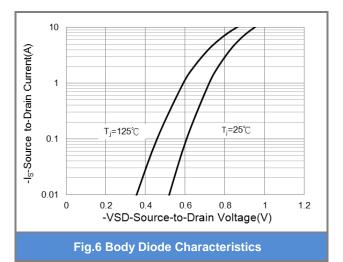


Fig.5 On-Resistance Variation with VGS.







#### **TYPICAL CHARACTERISTIC CURVES**

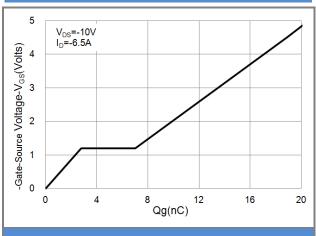


Fig.7 Gate-Charge Characteristics

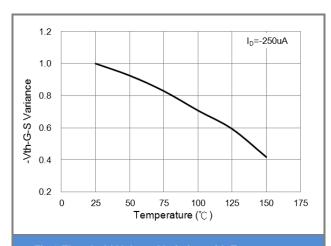


Fig.8 Threshold Voltage Variation with Temperature

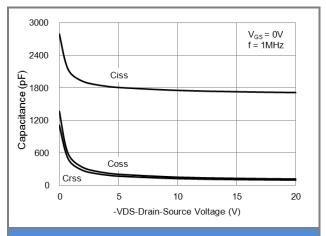


Fig.9 Threshold Voltage Variation with Temperature.

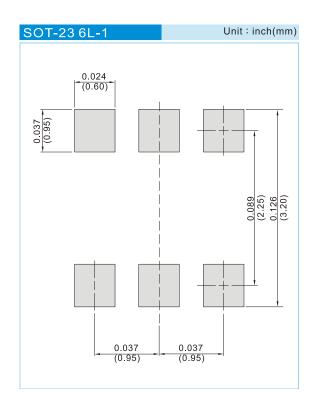




### PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJS6417_S1_00001	SOT-23 6L-1	3K pcs / 7" reel	S17	Halogen free RoHS compliant

## **MOUNTING PAD LAYOUT**







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